PATENT COOPERATION TREATY

PCT

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY (Chapter I of the Patent Cooperation Treaty)

(PCT Rule 44bis)

Applicant's or agent's file reference 00000PCT7502	FOR FURTHER ACTION	See item 4 below			
International application No. PCT/JP2004/016796	International filing date (day/month/year) 05 November 2004 (05.11.2004)	Priority date (day/month/year) 14 November 2003 (14.11.2003)			
International Patent Classification (8th edition unless older edition indicated) See relevant information in Form PCT/ISA/237					
Applicant SEMICONDUCTOR ENERGY LABORATORY CO., LTD.					

1.	This international preliminary report on patentability (Chapter I) is issued by the International Bureau on behalf of the International Searching Authority under Rule 44 bis.1(a).				
2.	This REPORT consists of a total of 6 sheets, including this cover sheet.				
	In the attached sheets, any reference to the written opinion of the International Searching Authority should be read as a reference to the international preliminary report on patentability (Chapter I) instead.				
3.	This report contains indications relating to the following items:				
	Box No. I	Basis of the report			
	Box No. II	Priority			
	Box No. III	Non-establishment of opinion with regard to novelty, inventive step and industrial applicability			
	Box No. IV	Lack of unity of invention			
	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industria applicability; citations and explanations supporting such statement				
	Box No. VI	Certain documents cited			
	Box No. VII	Certain defects in the international application			
	Box No. VIII	Certain observations on the international application			
4.	The International Bureau will communicate this report to designated Offices in accordance with Rules 44bis.3(c) and 93bis.1 but not, except where the applicant makes an express request under Article 23(2), before the expiration of 30 months from the priority date (Rule 44bis.2).				

Date of issuance of this report 15 May 2006 (15.05.2006) Authorized officer The International Bureau of WIPO 34, chemin des Colombettes 1211 Geneva 20, Switzerland Masashi Honda Telephone No. +41 22 338 70 10 Facsimile No. +41 22 740 14 35

Form PCT/IB/373 (January 2004)

PATENT COOPERATION TREATY

From the NTERNATIONAL SEARCHING AUTHORITY	REC'D 1 0 FEB 2005			
To: SEMICONDUCTOR ENERGY LABORATORY CO., LTD. 398, Hase, Atsugi-shi, Kanagawa 2430036 Japan	WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43bis.1)			
	Date of mailing (day/month/year) 08.02.2005			
Applicant's or agent's file reference	FOR FURTHER ACTION See paragraph 2 below			
00000PCT7502 International application No. International filing da	te (day/month/year) Priority date (day/month/year)			
Mitter Management - FF	14.11.2003			
International Patent Classification (IPC) or both national classification (IPC) are 120 / 795	ication and IPC			
Int.Cl 7 H01L29/786				
Applicant ENERGY LABORA	TORY CO. LTD.			
SEMICONDUCTOR ENERGY LABORA	TORT CO., LID.			
1. This opinion contains indications relating to the following items: Box No. I Basis of the opinion				
International Preliminary Examining Authority (TPEA) except that his does not apply which the apply which the special present that this one to be the IPEA and the chosen IPEA has notified the International Bureau under Rule 66.1bis(b) that written opinions of this International Searching Authority will not be so considered. If this opinion is, as provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA is a provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA is a provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA is a provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA is a provided above, considered to be a written opinion of the IPEA.				
PCT/ISA/220 or before the expiration of 22 months from the priority date, whichever expires later. For further options, see Form PCT/ISA/220.				
3. For further details, see notes to Form PCT/ISA/220.				
Date of completion of this opinion 25.01.2005				
Name and mailing address of the ISA/JP	Authorized officer 4L 9361			
Japan Patent Office	KAZUNARI TANADA			
3-4-3, Kasumigaseki, Chiyoda-ku, Tokyo 100-8915, Jar	Telephone No. +81-3-3581-1101 Ext. 3498			

Form PCT/ISA/237 (cover sheet) (January 2004)

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2004/016796

Box No. I	Basis of the opinion
which it wa	to the language, this opinion has been established on the basis of the international application in the language in a still file, unless otherwise indicated under this item. The opinion has been established on the basis of a translation from the original language into the following language which is the language of a translation furnished for the purposes of international search (under 12.3 and 23.1(b)).
With regard claimed inv	d to any nucleotide and/or amino acid sequence disclosed in the international application and necessary to the ention, this opinion has been established on the basis of:
a. type of n	naterial
	a sequence listing table(s) related to the sequence listing
	of material in written format in computer readable form
3.	filing/furnishing contained in the international application as filed. filed together with the international application in computer readable form. furnished subsequently to this Authority for the purposes of search. addition, in the case that more than one version or copy of a sequence listing and/or table relating thereto has been d or furnished, the required statements that the information in the subsequent or additional copies is identical to that the application as filed or does not go beyond the application as filed, as appropriate, were furnished.
4. Addition	al comments:
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1	

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2004/016796

Box No. IV	Lack of unity of invention
1. In resp	onse to the invitation (Form PCT/ISA/206) to pay additional fees the applicant has:
	paid additional fees
	paid additional fees under protest
V	not paid additional fees
pay a	Authority found that the requirement of unity of invention is not complied with and chose not to invite the applicant to idditional fees.
3. This Auth	ority considers that the requirement of unity of invention in accordance with Rule 13.1, 13.2 and 13.3 is
cor	nplied with
✓ not	complied with for the following reasons:
in res	nventions of claims 1-6 are linked to be one another only spect of the feature "at least one electrode is formed by a set discharge method". However, this feature is disclosed in or art document JP 2003-098548 A(HITACHI, LTD.), 04.03. So the feature cannot be a special technical feature.
inven	there exists no special technical feature linking the tions of claims 1-6 as to form a single general inventive ot among the inventions.
the c	efore there are no technical relationship which is dered as "special technical feature" (PCT rule 13.2) among laims 1-6. So this application contains the following s of invention which are not so linked as to form a single tive concept under PCT rule 13.2.
	roup I:Claims 1-4,7-10
6	roup II:Claims 5-6
	·
4. Conse	equently, this opinion has been established in respect of the following parts of the international application:
	all parts.
	the parts relating to claims Nos. 1-4,7-10

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No. PCT/JP2004/ 016796

Box No. V Reasoned statement under Rule 43bis.1(a)(i) with regard to novelty, inventive step or industrial applicability citations and explanations supporting such statement				
1.	Statement			
	Novelty (N)	Claims	1-4,7-10	YES NO
	•	Claims		NO
	(10)	Claims		YES
,	Inventive step (IS)	Claims	1-4,7-10	NO
			•	
Ind	Industrial applicability (IA)	Claims	1-4,7-10	YES NO
		Claims		NO

Citations and explanations

D1: JP 2002-217421 A(SEMICONDUCTOR ENERGY LABORATORY CO., LTD.), 2002.08.02, paragraphs [0021]-[0031], fig.1 (Family: none)

D2: JP 2003-098548 A(HITACHI, LTD.), 2003.04.03, paragraph [0016] (Family: none)

D3: JP 05-119351 A(SANYO ELECTRIC CO., LTD.), 1993.05.18, paragraphs [0002]-[0005], fig.7-12 (Family: none)

D4: JP 2003-059940 A(FUJI PHOTO FILM CO., LTD.),

2003.02.28, paragraphs [0022]-[0030](Family: none)

D5: JP 2003-241177 A(DAI NIPPON PRINTING CO., LTD), 2003.08.27,

paragraphs [0015]-[0032] (Family: none)

D6: JP 2003-149831 A(SEIKO EPSON CORPORATION),2003.05.21, paragraphs [0036]-[0045], fig.1 (Family: none)

Claims 1-3

The subject matters of claims 1, 2 and 3 do not appear to involve an inventive step in view of D1 and D2. D1 discloses a method for manufacturing a liquid crystal display device, comprising the steps of: forming a first electrode over a substrate; forming a first insulating film to cover the first electrode; forming a first semiconductor layer over the insulating film; forming a second insulating film over the first semiconductor layer to overlap the first electrode; forming an n-type second semiconductor layer to cover the second insulating film; patterning the first and second semiconductor layers into an island shape; forming a second and a third electrodes over the second semiconductor layer; etching the second semiconductor layer using the second and the third electrodes as a mask to be separated forming a fourth electrode to be in contact with the third electrode. D2 discloses a step of forming electrode by droplet discharge method. The thin film transistors in D1 and D2 are concerned with mutually related technical fields. Therefore, the skilled person in the art would easily conceive the idea of applying the technical feature employed in D2 to the invention disclosed in D1.

Claim 4

The subject matter of claim 4 does not appear to involve an inventive step in view of D1 , D2 and D3. D1 discloses a method for manufacturing a liquid crystal display device, comprising the steps of: forming a first electrode over a substrate; forming a first insulating film to cover the first electrode; forming a first semiconductor layer over the first insulating film; forming a second insulating film over the first semiconductor layer to overlap the first electrode; forming an n-type second semiconductor layer to cover the

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International application No.

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Supplemental Box

In case the space in any of the preceding boxes is not sufficient.

Continuation of: V.2

second insulating film; patterning the first and second semiconductor layers into an island shape; forming a third and a forth electrodes over the second semiconductor layer; etching the second semiconductor layer using the third and the forth electrodes as a mask to be separated. D3 discloses a step of forming a second electrode between the first insulating film and the first semiconductor layer. D2 discloses a step of forming electrode by droplet discharge method. The thin film transistors in D1, D2 and D3 are concerned with mutually related technical fields. Therefore, the skilled person in the art would easily conceive the idea of applying the technical features employed in D2 and D3 to the invention disclosed in D1.

Claims 7-8

The subject matters of claims 7 and 8 do not appear to involve an inventive step in view of D1, D2, D3, D4, D5 and D6. D4, D5 and D6 disclose base treatment before forming electrode. The methods for manufacturing a liquid crystal display device in D1, D2, D3, D4, D5 and D6 are concerned with mutually related technical fields. Therefore, the skilled person in the art would easily conceive the idea of applying the technical features employed in D2, D3, D4, D5 and D6 to the invention disclosed in D1.

Claim 9

The subject matter of claim 9 does not appear to involve an inventive step in view of D1, D2, D3 and D5. D5 discloses substance having photocatalytic function. The methods for manufacturing a liquid crystal display device in D1, D2, D3 and D5 are concerned with mutually related technical fields. Therefore, the skilled person in the art would easily conceive the idea of applying the technical features employed in D2, D3 and D5 to the invention disclosed in D1.

Claim 10

The subject matter of claim 10 does not appear to involve an inventive step in view of D1, D2, D3 and D6. D6 discloses plasma treatment as base treatment on a formation face to be liquid-repellent. The method for manufacturing a liquid crystal display device in D1, D2, D3 and D6 are concerned with mutually related technical fields. Therefore, the skilled person in the art would easily conceive the idea of applying the technical features employed in D2, D3, and D6 to the invention disclosed in D1.